

## NDT452P

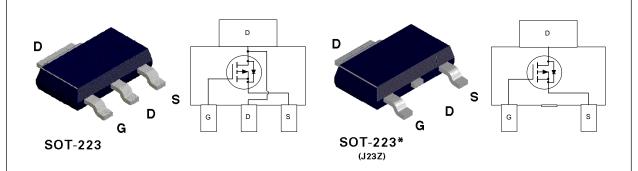
### P-Channel Enhancement Mode Field Effect Transistor

#### **General Description**

Power SOT P-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on-state resistance and provide superior switching performance. These devices are particularly suited for low voltage applications such as notebook computer power management and DC motor control.

#### **Features**

- -3A, -30V.  $R_{\text{DS(ON)}} = 0.18\Omega$  @  $V_{\text{GS}} = -10V$ .
- High density cell design for extremely low R<sub>DS(ON)</sub>.
- High power and current handling capability in a widely used surface mount package.



## **Absolute Maximum Ratings** $T_A = 25^{\circ}\text{C}$ unless otherwise noted

| Symbol                           | Parameter                               |           | NDT452P    | Units |
|----------------------------------|---|-----------|------------|-------|
| V <sub>DSS</sub>                 | Drain-Source Voltage                    |           | -30        | V     |
| V <sub>GSS</sub>                 | Gate-Source Voltage                     |           | ±20        | V     |
| I <sub>D</sub>                   | Drain Current - Continuous              | (Note 1a) | ±3         | А     |
|                                  | - Pulsed                                |           | ±20        |       |
| P <sub>D</sub>                   | Maximum Power Dissipation               | (Note 1a) | 3          | W     |
|                                  |   | (Note 1b) | 1.3        |       |
|                                  |   | (Note 1c) | 1.1        |       |
| T <sub>J</sub> ,T <sub>STG</sub> | Operating and Storage Temperature Rang  | je        | -65 to 150 | °C    |
| THERMA                           | AL CHARACTERISTICS                      |           |            |       |
| $R_{\theta JA}$                  | Thermal Resistance, Junction-to-Ambient | (Note 1a) | 42         | °C/W  |
| R <sub>OJC</sub>                 | Thermal Resistance, Junction-to-Case    | (Note 1)  | 12         | °C/W  |

<sup>\*</sup> Order option J23Z for cropped center drain lead.

| Symbol                | Parameter                         | Conditions  |  | Min   | Тур  | Max  | Units |
|-----------------------|-----------------------------------|---|--|-------|------|------|-------|
| OFF CHA               | RACTERISTICS                      |   |  | •     |      |      | •     |
| BV <sub>DSS</sub>     | Drain-Source Breakdown Voltage    | $V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$  |  | -30   |      |      | V     |
| I <sub>DSS</sub>      | Zero Gate Voltage Drain Current   | $V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}$    | $V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}$           |       |      |      |       |
|                       |                                   |   | T <sub>J</sub> = 55°C                                    |       |      | -25  | μA    |
| I <sub>GSSF</sub>     | Gate - Body Leakage, Forward      | $V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$     | •  |       |      | 100  | nA    |
| I <sub>GSSR</sub>     | Gate - Body Leakage, Reverse      | V <sub>GS</sub> = -20 V, V <sub>DS</sub> = 0 V    |  |       |      | -100 | nA    |
| ON CHAR               | ACTERISTICS (Note 2)              | ·   |  |       |      |      |       |
| $V_{GS(th)}$          | Gate Threshold Voltage            | $V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$       |  | -1    | -2   | -3   | V     |
|                       |                                   |   | T <sub>J</sub> =125°C                                    | -0.85 | -1.7 | -2.6 |       |
| R <sub>DS(ON)</sub>   | Static Drain-Source On-Resistance | $V_{GS} = -10 \text{ V}, I_{D} = -3 \text{ A}$    | •  |       | 0.15 | 0.18 | Ω     |
|                       |                                   |   | T <sub>J</sub> =125°C                                    |       | 0.23 | 0.32 |       |
|                       |                                   | $V_{GS} = -4.5 \text{ V}, I_{D} = -2.2 \text{ A}$ | $V_{GS} = -4.5 \text{ V}, I_{D} = -2.2 \text{ A}$        |       |      |      |       |
| I <sub>D(on)</sub>    | On-State Drain Current            | $V_{GS} = -10 \text{ V}, V_{DS} = -5 \text{ V}$   | -15  |       |      | Α    |       |
|                       |                                   | $V_{GS} = -4.5 \text{ V}, V_{DS} = -5 \text{ V}$  | -4.5   |       |      |      |       |
| g <sub>FS</sub>       | Forward Transconductance          | $V_{DS} = -15 \text{ V}, I_{D} = -3 \text{ A}$    |  | 3.7   |      | S    |       |
| DYNAMIC               | CHARACTERISTICS                   |   |  |       |      |      |       |
| C <sub>iss</sub>      | Input Capacitance                 | $V_{DS} = -10 \text{ V}, \ V_{GS} = 0 \text{ V},$ |  |       |      |      | pF    |
| C <sub>oss</sub>      | Output Capacitance                | f = 1.0 MHz                                       |  |       | 300  |      | pF    |
| C <sub>rss</sub>      | Reverse Transfer Capacitance      |   |  |       | 130  |      | pF    |
| SWITCHIN              | NG CHARACTERISTICS (Note 2)       |   |  |       |      |      |       |
| $\mathbf{t}_{D(on)}$  | Turn - On Delay Time              | $V_{DD} = -10 \text{ V}, I_{D} = -1.0 \text{ A},$ |  |       |      |      | ns    |
| t <sub>r</sub>        | Turn - On Rise Time               | $V_{GEN}$ = -10 V, $R_{GEN}$ = 6 $\Omega$         |  | 15    | 40   | ns   |       |
| $\mathbf{t}_{D(off)}$ | Turn - Off Delay Time             |   |  | 25    | 90   | ns   |       |
| t,                    | Turn - Off Fall Time              |   |  |       | 8    | 50   | ns    |
| $Q_g$                 | Total Gate Charge                 | $V_{DS} = -10 \text{ V},$                         |  |       | 15   | 25   | nC    |
| $Q_{gs}$              | Gate-Source Charge                | $I_D = -3 \text{ A}, \ V_{GS} = -10 \text{ V}$    | $I_{\rm D} = -3  \text{A}, \ V_{\rm GS} = -10  \text{V}$ |       |      | 4    | nC    |
| $Q_{gd}$              | Gate-Drain Charge                 |   |  |       | 4.5  | 8    | nC    |

| Electrical Characteristics (T <sub>A</sub> = 25°C unless otherwise noted) |   |  |  |  |      |   |  |  |  |  |
|---|---|--|--|--|------|---|--|--|--|--|
| Symbol  | Parameter Conditions Min Typ Max Units                                      |  |  |  |      |   |  |  |  |  |
| DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS                    |   |  |  |  |      |   |  |  |  |  |
| Is  | I <sub>s</sub> Maximum Continuous Drain-Source Diode Forward Current -2.5 A |  |  |  |      |   |  |  |  |  |
| V <sub>SD</sub>   | Drain-Source Diode Forward Voltage  | $V_{GS} = 0 \text{ V}, \ I_{S} = -3 \text{ A} \ \text{(Note 2)}$ |  |  | -1.2 | V |  |  |  |  |

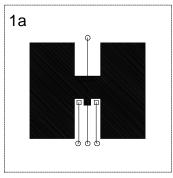
#### Notes:

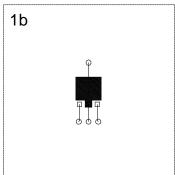
1.  $R_{g,A}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{g,C}$  is guaranteed by design while  $R_{g,C,A}$  is determined by the user's board design.

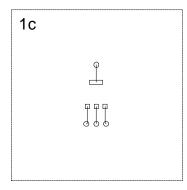
$$P_D(t) = \frac{T_J - T_A}{R_{\theta J} \dot{A}^{\dagger}} = \frac{T_J - T_A}{R_{\theta J} \dot{A}^{\dagger} R_{\theta C} \dot{A}^{\dagger}} = I_D^2(t) \times R_{DS(ON) \theta T_J}$$

Typical  $R_{\theta_{JA}}$  using the board layouts shown below on 4.5"x5" FR-4 PCB in a still air environment:

- a. 42°C/W when mounted on a 1 in² pad of 2oz copper.
- b. 95°C/W when mounted on a 0.066 in  $^{\!2}$  pad of 2oz copper.
- c. 110°C/W when mounted on a 0.0123 in² pad of 2oz copper.



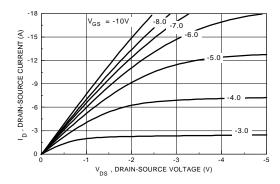




Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width  $\leq$  300 $\mu$ s, Duty Cycle  $\leq$  2.0%.

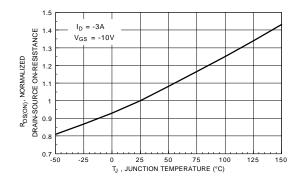
## **Typical Electrical Characteristics**



3 V<sub>GS</sub> = -4.0V V<sub>GS</sub> = -4.5V V<sub>GS</sub> = -4.5V

Figure 1. On-Region Characteristics.

Figure 2. On-Resistance Variation with Gate Voltage and Drain Current.



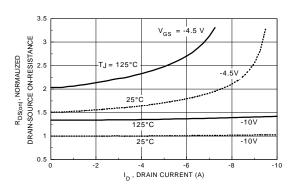
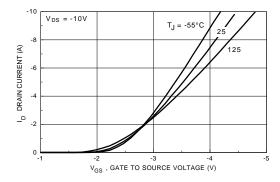


Figure 3. On-Resistance Variation with Temperature.

Figure 4. On-Resistance Variation with Drain Current and Temperature.



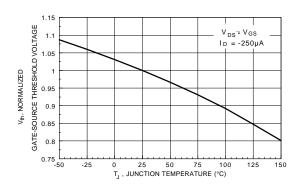


Figure 5. Transfer Characteristics.

Figure 6. Gate Threshold Variation with Temperature.

## **Typical Electrical Characteristics (continued)**

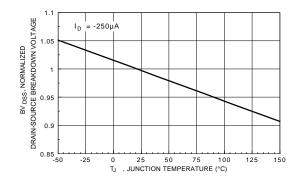
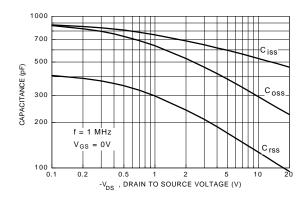


Figure 7. Breakdown Voltage Variation with Temperature.

Figure 8. Body Diode Forward Voltage Variation with Current and Temperature.



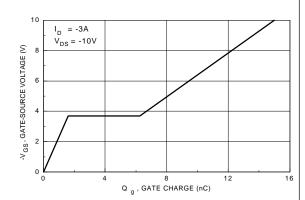
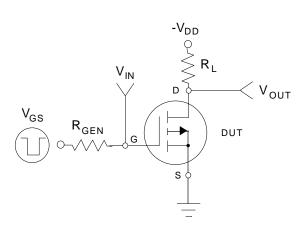


Figure 9. Capacitance Characteristics.

Figure 10. Gate Charge Characteristics.



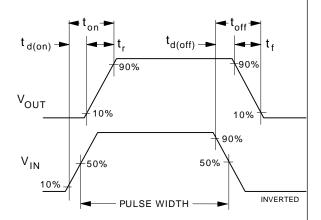
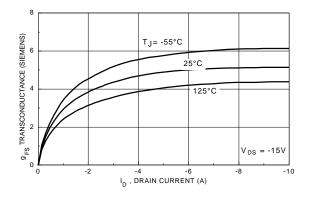


Figure 11. Switching Test Circuit.

Figure 12. Switching Waveforms.

## **Typical Electrical Characteristics (continued)**



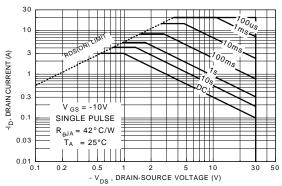


Figure 13. Transconductance Variation with Drain **Current and Temperature.** 

Figure 14. Maximum Safe Operating Area.

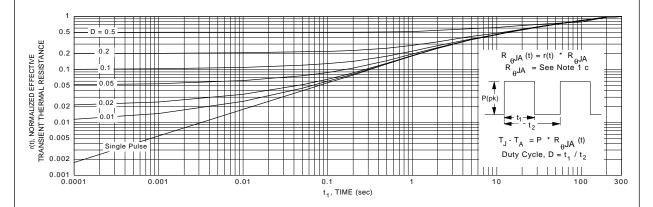


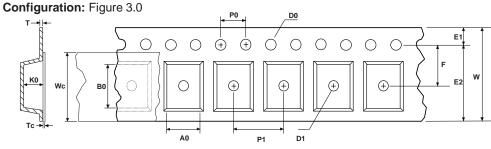
Figure 15. Transient Thermal Response Curve.

Note: Thermal characterization performed using the conditions described in note 1c. Transient thermal response will change depending on the circuit board design.





## **SOT-223 Embossed Carrier Tape**



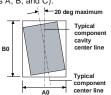
| User Direction of Feed |               |
|------------------------|---------------|
|                        | $\overline{}$ |

| Dimensions are in millimeter |                 |                 |                |                 |                 |                 |              |                 |               |               |                 |                        |                 |                 |
|------------------------------|-----------------|-----------------|----------------|-----------------|-----------------|-----------------|--------------|-----------------|---------------|---------------|-----------------|------------------------|-----------------|-----------------|
| Pkg type                     | Α0              | В0              | w              | D0              | D1              | E1              | E2           | F               | P1            | P0            | K0              | Т                      | Wc              | Тс              |
| <b>SOT-223</b> (12mm)        | 6.83<br>+/-0.10 | 7.42<br>+/-0.10 | 12.0<br>+/-0.3 | 1.55<br>+/-0.05 | 1.50<br>+/-0.10 | 1.75<br>+/-0.10 | 10.25<br>min | 5.50<br>+/-0.05 | 8.0<br>+/-0.1 | 4.0<br>+/-0.1 | 1.88<br>+/-0.10 | 0.292<br>+/-<br>0.0130 | 9.5<br>+/-0.025 | 0.06<br>+/-0.02 |

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation

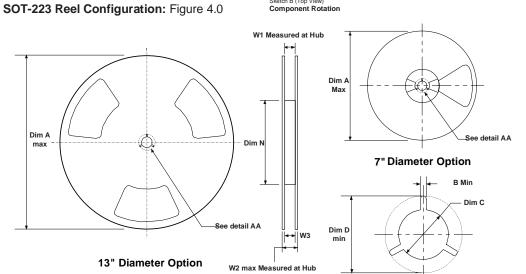


Sketch B (Top View)
Component Rotation



Sketch C (Top View)
Component lateral movement

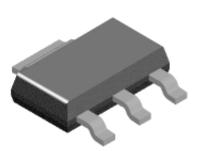
DETAIL AA

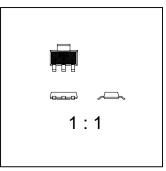


|           | Dimensions are in inches and millimeters |               |              |                                   |               |              |                                  |               |                              |
|-----------|--|---------------|--------------|-----------------------------------|---------------|--------------|----------------------------------|---------------|------------------------------|
| Tape Size | Reel<br>Option                           | Dim A         | Dim B        | Dim C                             | Dim D         | Dim N        | Dim W1                           | Dim W2        | Dim W3 (LSL-USL)             |
| 12mm      | 7" Dia                                   | 7.00<br>177.8 | 0.059<br>1.5 | 512 +0.020/-0.008<br>13 +0.5/-0.2 | 0.795<br>20.2 | 5.906<br>150 | 0.488 +0.078/-0.000<br>12.4 +2/0 | 0.724<br>18.4 | 0.469 - 0.606<br>11.9 - 15.4 |
| 12mm      | 13" Dia                                  | 13.00<br>330  | 0.059<br>1.5 | 512 +0.020/-0.008<br>13 +0.5/-0.2 | 0.795<br>20.2 | 7.00<br>178  | 0.488 +0.078/-0.000<br>12.4 +2/0 | 0.724<br>18.4 | 0.469 - 0.606<br>11.9 - 15.4 |

## SOT-223 Tape and Reel Data and Package Dimensions, continued

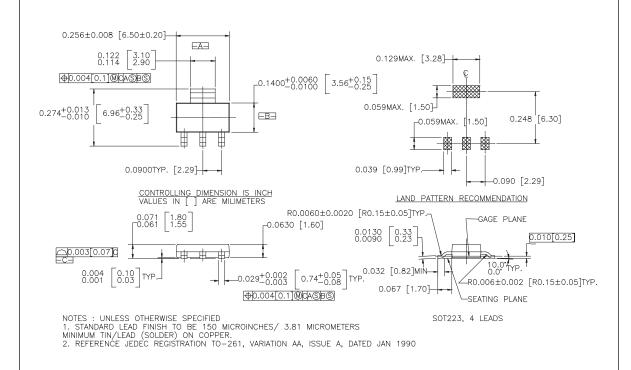
# SOT-223 (FS PKG Code 47)





Scale 1:1 on letter size paper

Part Weight per unit (gram): 0.1246



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